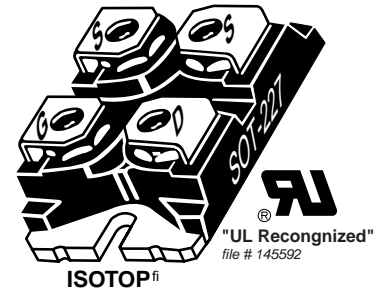


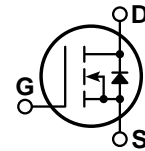
POWER MOS V[®]

Power MOS V[®] is a new generation of high voltage N-Channel enhancement mode power MOSFETs. This new technology minimizes the JFET effect, increases packing density and reduces the on-resistance. Power MOS V[®] also achieves faster switching speeds through optimized gate layout.



- **Faster Switching**
- **100% Avalanche Tested**
- **Lower Leakage**
- **Popular SOT-227 Package**

Unless stated otherwise, Microsemi discrete MOSFETs contain a single MOSFET die. This device is made with two parallel MOSFET die. It is intended for switch-mode operation. It is not suitable for linear mode operation.



MAXIMUM RATINGS

All Ratings: $T_C = 25^\circ\text{C}$ unless otherwise specified.

Symbol	Parameter	APT50M85JVR	UNIT
V_{DSS}	Drain-Source Voltage	500	Volts
I_D	Continuous Drain Current @ $T_C = 25^\circ\text{C}$	50	Amps
I_{DM}	Pulsed Drain Current ^①	200	
V_{GS}	Gate-Source Voltage Continuous	± 30	Volts
V_{GSM}	Gate-Source Voltage Transient	± 40	
P_D	Total Power Dissipation @ $T_C = 25^\circ\text{C}$	500	Watts
	Linear Derating Factor	4	W/ $^\circ\text{C}$
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to 150	$^\circ\text{C}$
T_L	Lead Temperature: 0.063" from Case for 10 Sec.	300	
I_{AR}	Avalanche Current ^① (Repetitive and Non-Repetitive)	30	Amps
E_{AR}	Repetitive Avalanche Energy ^①	30	mJ
E_{AS}	Single Pulse Avalanche Energy ^④	1300	

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
BV_{DSS}	Drain-Source Breakdown Voltage ($V_{GS} = 0V, I_D = 250\mu\text{A}$)	500			Volts
$I_{D(on)}$	On State Drain Current ^② ($V_{DS} > I_{D(on)} \times R_{DS(on)}$ Max, $V_{GS} = 10V$)	50			Amps
$R_{DS(on)}$	Drain-Source On-State Resistance ^② ($V_{GS} = 10V, 0.5 I_{D[Cont.]}$)			0.085	Ohms
I_{DSS}	Zero Gate Voltage Drain Current ($V_{DS} = V_{DSS}, V_{GS} = 0V$)			50	μA
	Zero Gate Voltage Drain Current ($V_{DS} = 0.8 V_{DSS}, V_{GS} = 0V, T_C = 125^\circ\text{C}$)			500	
I_{GSS}	Gate-Source Leakage Current ($V_{GS} = \pm 30V, V_{DS} = 0V$)			± 100	nA
$V_{GS(th)}$	Gate Threshold Voltage ($V_{DS} = V_{GS}, I_D = 1\text{mA}$)	2		4	Volts

 **CAUTION:** These Devices are Sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

DYNAMIC CHARACTERISTICS

APT50M85JVR

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
C_{iss}	Input Capacitance	$V_{GS} = 0V$ $V_{DS} = 25V$ $f = 1\text{ MHz}$		9000	10800	pF
C_{oss}	Output Capacitance			1240	1740	
C_{rss}	Reverse Transfer Capacitance			500	750	
Q_g	Total Gate Charge ③	$V_{GS} = 10V$ $V_{DD} = 0.5 V_{DSS}$ $I_D = 0.5 I_{D[Cont.]}$ @ 25°C		390	535	nC
Q_{gs}	Gate-Source Charge			42	65	
Q_{gd}	Gate-Drain ("Miller") Charge			170	255	
$t_{d(on)}$	Turn-on Delay Time	$V_{GS} = 15V$ $V_{DD} = 0.5 V_{DSS}$ $I_D = I_{D[Cont.]}$ @ 25°C $R_G = 0.6\Omega$		15	30	ns
t_r	Rise Time			17	34	
$t_{d(off)}$	Turn-off Delay Time			52	80	
t_f	Fall Time			7	14	

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
I_S	Continuous Source Current (Body Diode)			50	Amps
I_{SM}	Pulsed Source Current ① (Body Diode)			200	
V_{SD}	Diode Forward Voltage ② ($V_{GS} = 0V, I_S = -I_{D[Cont.]}$)			1.3	Volts
t_{rr}	Reverse Recovery Time ($I_S = -I_{D[Cont.]}, di_S/dt = 100A/\mu s$)		690		ns
Q_{rr}	Reverse Recovery Charge ($I_S = -I_{D[Cont.]}, di_S/dt = 100A/\mu s$)		18		μC

THERMAL/PACKAGE CHARACTERISTICS

Symbol	Characteristic	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction to Case			0.25	$^{\circ}C/W$
$R_{\theta JA}$	Junction to Ambient			40	
$V_{isolation}$	RMS Voltage (50-60 Hz Sinusoidal Waveform From Terminals to Mounting Base for 1 Min.)	2500			Volts
Torque	Maximum Torque for Device Mounting Screws and Electrical Terminations.			13	lb•in

① Repetitive Rating: Pulse width limited by maximum junction temperature.

③ See MIL-STD-750 Method 3471

② Pulse Test: Pulse width < 380 μs , Duty Cycle < 2%

④ Starting $T_j = +25^{\circ}C$, $L = 2.89mH$, $R_G = 25\Omega$, Peak $I_L = 30A$

Microsemi reserves the right to change, without notice, the specifications and information contained herein.

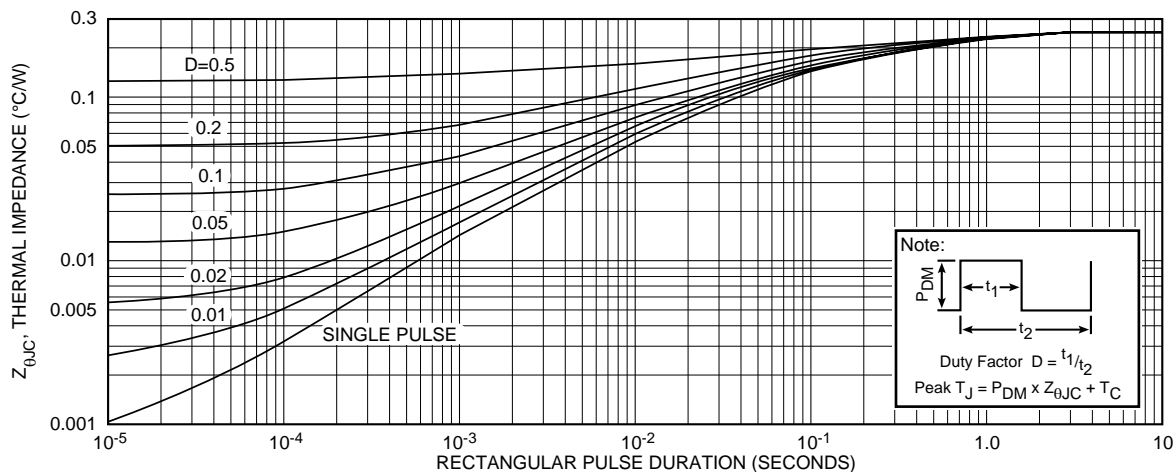


FIGURE 1, MAXIMUM EFFECTIVE TRANSIENT THERMAL IMPEDANCE, JUNCTION-TO-CASE vs PULSE DURATION

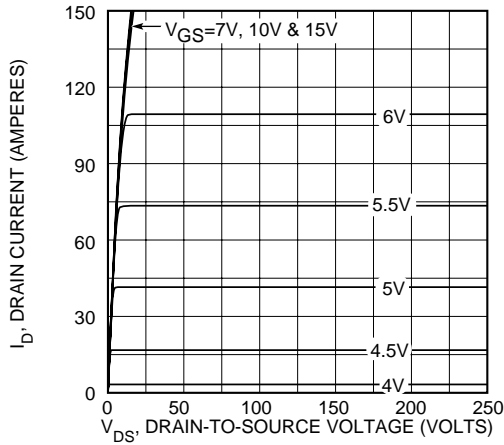


FIGURE 2, TYPICAL OUTPUT CHARACTERISTICS

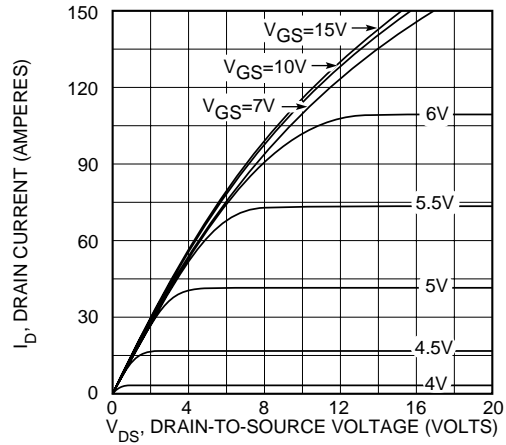


FIGURE 3, TYPICAL OUTPUT CHARACTERISTICS

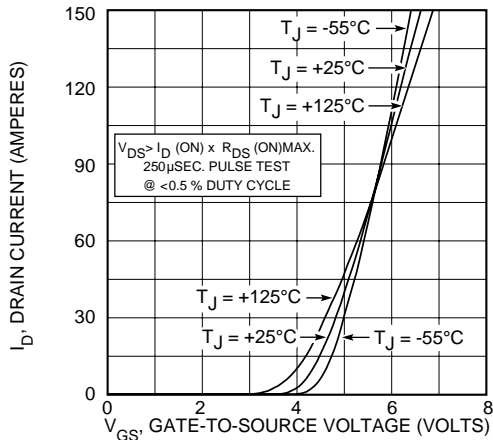


FIGURE 4, TYPICAL TRANSFER CHARACTERISTICS

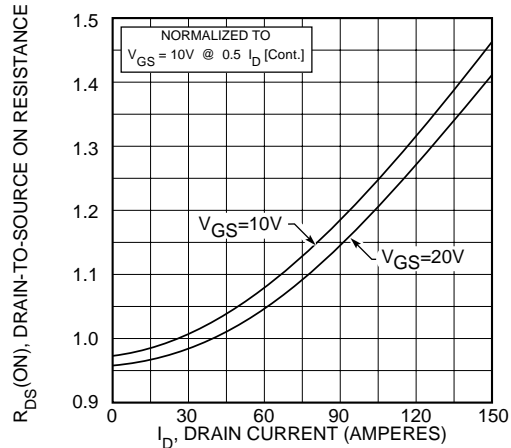


FIGURE 5, $R_{DS(ON)}$ vs DRAIN CURRENT

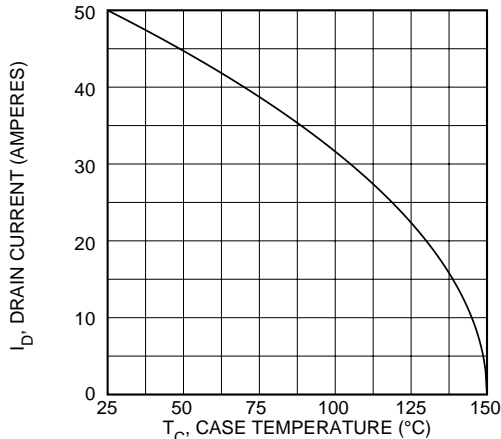


FIGURE 6, MAXIMUM DRAIN CURRENT vs CASE TEMPERATURE

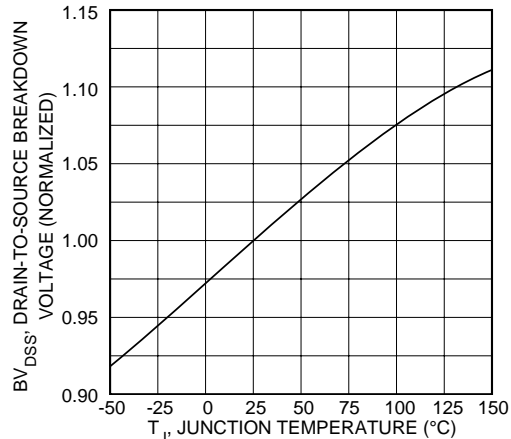


FIGURE 7, BREAKDOWN VOLTAGE vs TEMPERATURE

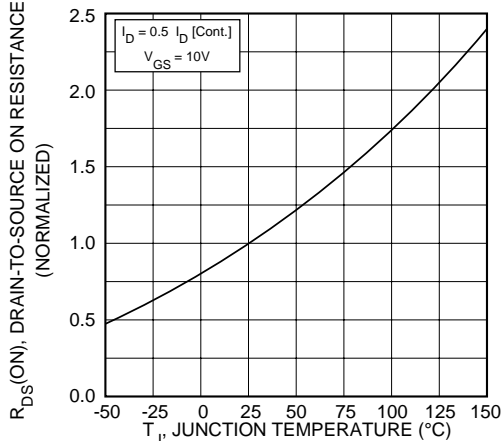


FIGURE 8, ON-RESISTANCE vs. TEMPERATURE

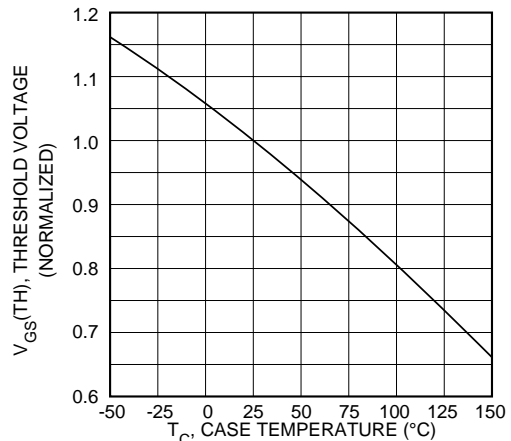


FIGURE 9, THRESHOLD VOLTAGE vs TEMPERATURE

I_D DRAIN CURRENT (AMPERES)

Graph removed

V_{DS} DRAIN-TO-SOURCE VOLTAGE (VOLTS)
FIGURE 10, MAXIMUM SAFE OPERATING AREA

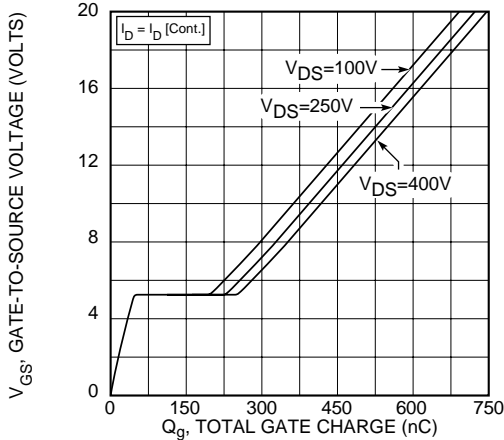


FIGURE 12, GATE CHARGES vs GATE-TO-SOURCE VOLTAGE

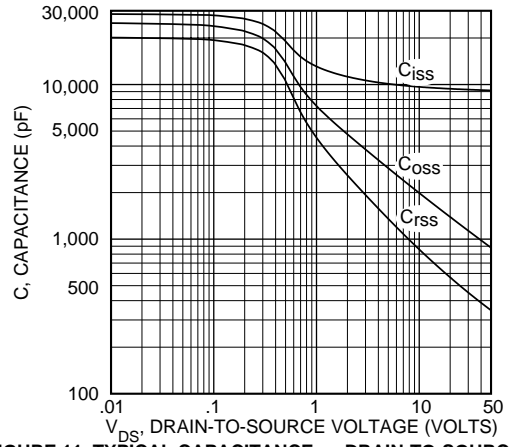


FIGURE 11, TYPICAL CAPACITANCE vs DRAIN-TO-SOURCE VOLTAGE

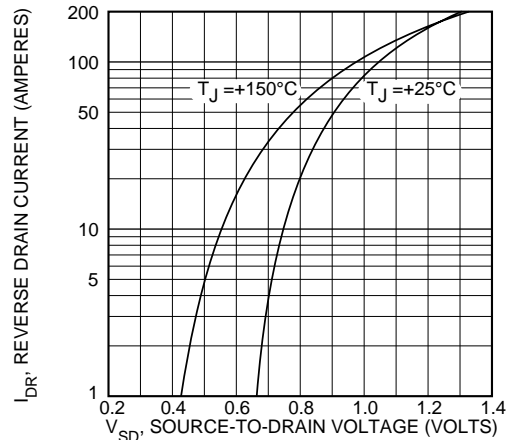
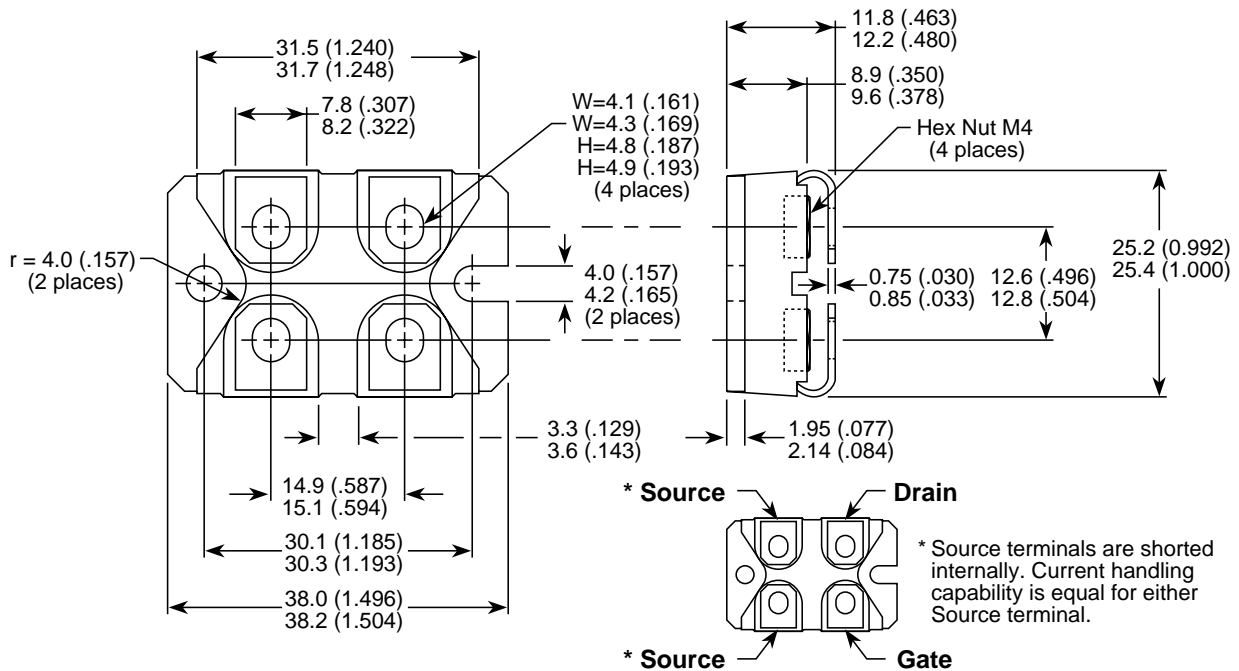


FIGURE 13, TYPICAL SOURCE-DRAIN DIODE FORWARD VOLTAGE

SOT-227 (ISOTOP®) Package Outline



Dimensions in Millimeters and (Inches)